

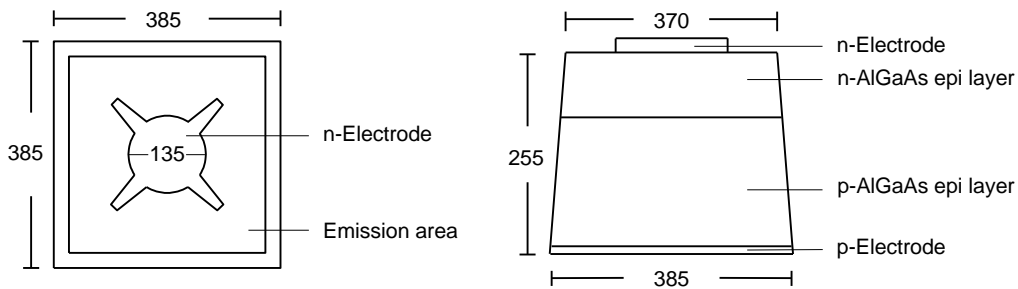
■ Features :

- N Side Up

■ Typical Applications :

- Industrial Infrared Equipment

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	385 μm x 385 μm
	Thickness	255 μm
	Emission area	370 μm
	Bonding pad	135 μm
Electrode	Top: N (cathode)	Gold
	Backside: P (anode)	Gold alloy
Surface condition	Smooth	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	1.31	1.50	V
		$I_F = 100 \text{ mA}$	-	1.52	-	
Reverse Voltage	V_R	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	λ_p	$I_F = 20 \text{ mA}$	870	880	910	nm
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	70	-	nm
Radiant Power	P_o	$I_F = 20 \text{ mA}$	0.40	0.86	-	mW

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

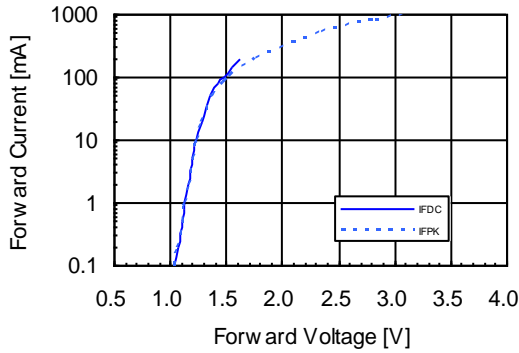


Fig 2. Relative Radiant Power vs. Wavelength

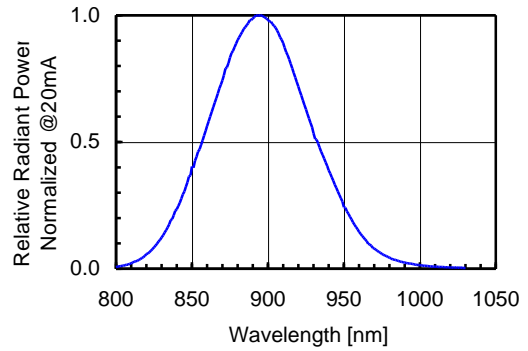


Fig 3. Relative Radiant Power vs. Forward DC Current

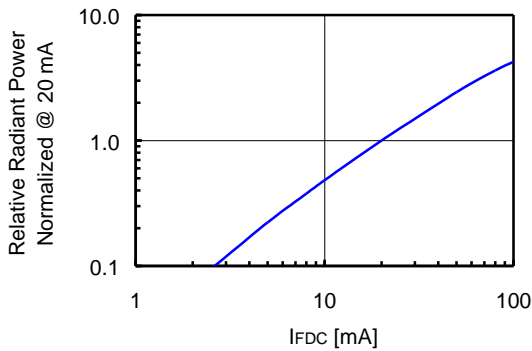


Fig 4. Relative Radiant Power vs. Forward Peak Current

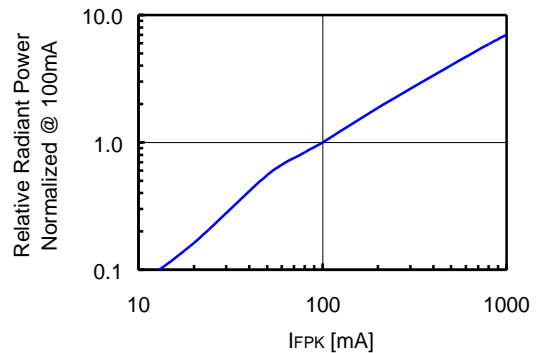


Fig 5. Forward DC Voltage vs. Temperature

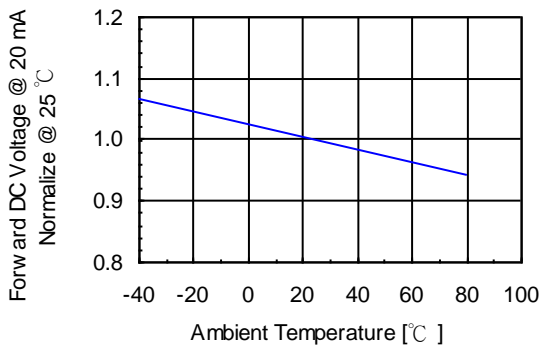


Fig 6. Relative Radiant Power vs. Temperature

